



BC857CQ

45V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Description

This Bipolar Junction Transistors (BJT) are designed to meet the stringent requirements of Automotive Applications.

Features

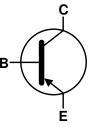
- Ideally Suited for Automatic Insertion
- Complementary NPN Types: BC847CQ
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

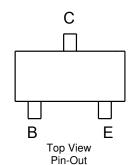
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208⁽³⁾
- Weight: 0.008 grams (Approximate)







Device Symbol



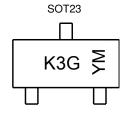
Ordering Information (Note 5)

Part Number	Compliance	Marking	Reel Size (inches)	Quantity per Reel
BC857CQ-7-F	Automotive	K3G	7	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K3G = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2017	20)18	2019	2	020	2021		2022	2023		2024
Code	E		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	/ Dec



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Continuous Collector Current	I _C	-100	mA
Peak Collector Current	Ісм	-200	mA
Peak Emitter Current	I _{EM}	-200	mA
Peak Base Current	I _{BM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	р	310	mW	
Power Dissipation	(Note 7)	$ P_D$	350	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 6)	В	403	°C/W	
Thermal nesistance, junction to Ambient	(Note 7)	R _{eJA}	357	G/VV	
Thermal Resistance, Junction to Leads	(Note 8)	R ₀ JL	350	°C/W	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-65 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

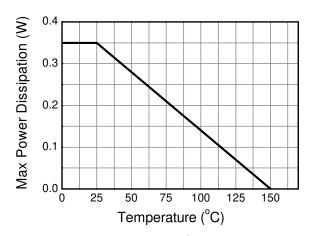
Notes:

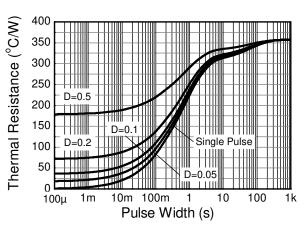
- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except the device is mounted on 15mm x 15mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the leads).

 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



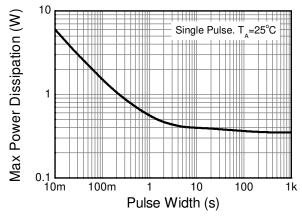
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation



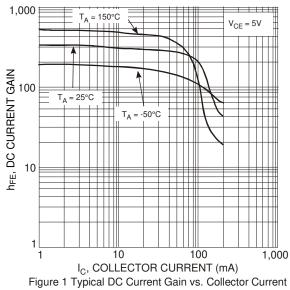
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

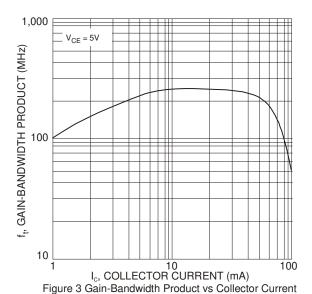
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	_	I	V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	-45	_		٧	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	1	٧	$I_E = -1\mu A$
Collector Cutoff Current	1			-15	nA	$V_{CB} = -30V$
Collector Cuton Current	Ісво	_	_	-4	μΑ	$V_{CB} = -30V, T_{J} = +150^{\circ}C$
Collector Emitter Cutoff Current	I _{CES}		_	-15	nA	V _{CE} = -50V
Emitter-Base Cutoff Current	I _{EBO}		_	-100	nA	V _{EB} = -5V
Small Signal Current Gain (Note 10)	h _{fe}	1	600	1	ı	
Input Impedance (Note 10)	h _{ie}	_	8.7	_	kΩ	$I_{C} = -2.0 \text{mA}, V_{CE} = -5 \text{V}$
Output Admittance (Note 10)	h _{oe}	1	60	1	μS	f = 1.0kHz
Reverse Voltage Transfer Ratio (Note 10)	h _{re}	_	3x10 ⁻⁴	_	_	
DC Current Gain (Note 10)	h _{FE}	420	520	800	_	$I_C = -2.0 \text{mA}, V_{CE} = -5 \text{V}$
Callactor Emitter Saturation Voltage (Note 10)	W		-75	-300	mV	$I_C = -10mA$, $I_B = -0.5mA$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)}	_	-250	-650	IIIV	$I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Turn-On Voltage (Note 10)	V	-600	-650	-750	mV	$I_C = -2mA, V_{CE} = -5V$
Base-Emiller Fulli-On Voltage (Note 10)	V _{BE(ON)}	1	_	-820	IIIV	$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$
Base-Emitter Saturation Voltage (Note 10)			-700		mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
Base-Emiller Saturation Voltage (Note 10)	$V_{BE(SAT)}$	_	-850	-1100	IIIV	$I_C = -100 \text{mA}, I_B = -5 \text{mA}$
Output Capacitance	Сово		3	I	рF	$V_{CB} = -10V, f = 1.0MHz$
Transition Frequency	f _T	100	200	1	MHz	$V_{CE} = -5V$, $I_{C} = -10mA$, $f = 100MHz$
Noise Figure	NF		2	10	dB	$V_{CE} = -5V, \ I_C = -200 \mu A$ $R_S = 2k\Omega, \ f = 1kHz$ $\Delta f = 200Hz$

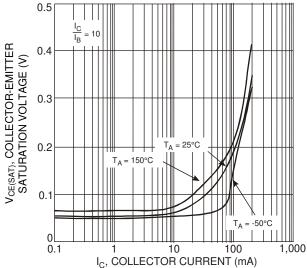
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







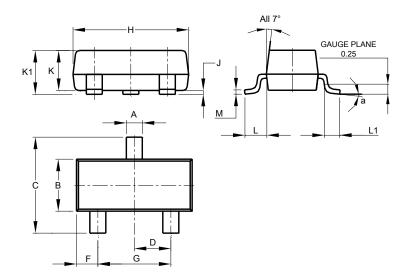
I_C, COLLECTOR CURRENT (mA)
Figure 2 Typical Collector-Emitter Saturation Voltage
vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

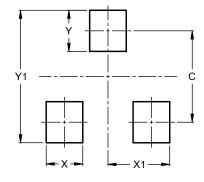


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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